

FEATURES

- 45 mΩ High-Side MOSFET
- 3.1A continuous current capability in EMSOP8
- 1.0~4.0 A (typ.) Adjustable Current Limit
- ±7.5% Current Limited Accurate at 3.1A
- Meet Apple® Current Requirements
- Low Average Current in OUT shorted GND
- Support Apple® Devices fast charging (Apple® 2.1A / 2.4A mode)
- Support Samsung Galaxy Tab Devices fast Charging
- Support BC1.2 & YD/T 1591-2009 Charging Spec
- Built-in Soft-Start
- Support single layer PCB layout.
- 4.5 ~ 6.5V Single Supply Operation.
- Available EMSOP8 package.

APPLICATIONS

- USB Charger
- USB Wall Adapter
- Car Charger

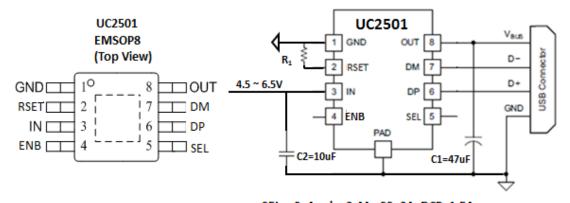
DESCRIPTION

The UC2501 integrated USB charger emulators with automatic host charger identification circuitry and high performance adjustable current limiting power switch. An automatic USB charger identification circuit allows mobile power supply can automatically provides the correct modes on the data lines to charger compliant devices among the Apple, Samsung and BC1.2 modes.

The UC2501 is a $45m\Omega$ power switch intended for applications where heavy capacitive loads and short-circuits are likely to be encountered. This also provides hiccup mode when OUT voltage is less than 2.85V or OTSD.

The UC2501 provides an ENB pin to turn on or turn off UC2501 and an SEL pin to select 10W or 12W mode in application.

PACKAGE AND APPLICATION



SEL = 0: Apple=2.4A, SS=2A, DCP=1.5A;

SEL = 1 or Floating: Apple=2.1A, SS=2A, DCP=1.5A;

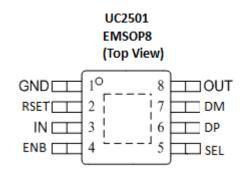
ENB is floating or pull down with 10k Resistor if not used

ORDING INFORMATION

Part Number	Package Type	Package Qty	Op Temp(°C)	Mark
UC2501	EMSOP8	3000	-40~85	UC2501



PINOUT



PIN FUNCTIONS

NO.	NAME	TYPE ⁽¹⁾	DESCRIPTION
1	GND	G	Ground connection
2	RSET	I	External resistor used to set current-limit threshold; recommended 13 $K\Omega \le R_{SET} \le 100 K\Omega$;
3	IN	P/I	Power supply/Input voltage connected to Power Switch; connect a 1 µF or greater ceramic capacitor from IN to GND as close to the IC as possible
4	ENB	I	Enable input, logic low turns on UC2501
5	SEL	I	Logic-level control input; When it is high or floating, DP/DM operate in 2.1A mode, when it is Low, DP/DM operate in 2.4A mode;
6	DP	O/I	DP date line to connector, output for hand-shake voltage to portable equipment, high impedance while disabled
7	DM	O/I	DM data line to connector, input for hand-shake voltage from portable equipment high impedance while disabled
8	OUT	0	Power-switch output, connected to VBUS of USB; connect a 22µF or greater ceramic capacitor from OUT to GND as close to the IC as possible

⁽¹⁾ G = Ground, I = Input, O = Output, P = Power



ABSOLUTE MAXIMUM RATINGS (1)

Over recommended operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT		
Supply Voltage Range	IN	-0.3	7.0	V	
Input voltage range	DP,DM	-0.3	5.8		
Continuous output sink current	DP input current, DM input current		35	A	
Continuous output source current	DP output current, DM output current		35	- mA	
ESD rating, Human Body	IN		2	- kV	
Model (HBM)	DP, DM		2		
ESD rating, Charging Device Model (CDM)			500	V	
Operating Junction Temperature	T _J	-40	125	°C	
Storage Temperature Range	T _{stg}	-65	150		

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	THERMAL METRIC		
θ_{JA}	EMSOP8 Package thermal impedance ⁽¹⁾	65	°C/W

⁽¹⁾ The package thermal impedance is calculated in accordance with JESD 51-7.

RECOMMENDED OPERATING CONDITIONS

	PARAMETER	MIN	MAX	UNIT	
V _{IN}	Input voltage of IN	4.5	6.5	V	
V _{DP/DM}	DP data line input voltage		5.5	V	
I _{DP/DM}	Continuous sink/source current		±10	mA	
R _{SET}	Resistance of R _{SET}	13	100	kΩ	
I _{OUT}	Continuous sink/source current	1000	4000	mA	
TJ	Operating Junction Temperature	-40	125	°C	



ELECTRICAL CHARACTERISTICS

Conditions are $-40^{\circ}\text{C} \le (\text{TJ} = \text{TA}) \le 125^{\circ}\text{C}$, $4.5 \text{ V} \le \text{VIN} \le 6.5 \text{ V}$, VSEL = VIN and RSET = 68.1 k Ω . Positive current are into pins. Typical values are at 25°C. All voltages are with respect to GND (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Power Switch						
RDSON	Drain-source on-state resitance	Iout=1A		45	68	mΩ
Tr	OUT voltage rise time		1.73			
Tf	OUT voltage fall time	0 4 5 D 400 0	0.8			
Ton	OUT voltage turn-on time	$C_L = 1 \mu F, R_L = 100 \Omega,$		2.48		ms
Toff	OUT voltage turn-off time			2.98		
Current Limit	•	•				
		Rset=13.0k	3.77	4.05	4.33	
		Rset=15.4k	3.15	3.41	3.66	
		Rset=19.1k	2.50	2.74	3.00	A
los	OUT current limited	Rset=20.0k	2.40	2.65	2.90	
		Rset=21.5k	2.20	2.43	2.60	
		Rset=22.6k	2.10	2.32	2.50	
Enable Pin (EN	3)		-1			- 1
V _{ENB}	ENB threshold voltage, falling		0.8	1.33	2.3	V
V _{ENB_HYS}	Hysteresis			150		mV
R _{PD}	Pull Down Resistor		200	290	380	kΩ
Hiccup Mode	•	•				
Vout_short	OUT Threshold Voltage to enter Hiccup mode			2.85		V
Ton_HICCUP	ON Time of Hiccup mode		70	130	190	ms
Toff_HICCUP	OFF Time of Hiccup mode		0.7	1.3	1.9	s
Thermal Shutdown						
	Temperature Rising Threshold			172		°C
	Hysteresis			20		



ELECTRICAL CHARACTERISTICS

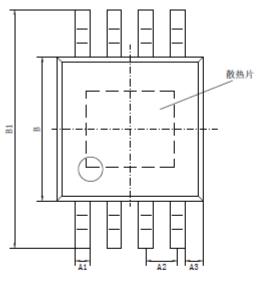
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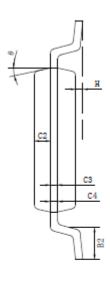
P	ARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
UNDERVOLTAGE L	оскоит		1			
Vuvlo	IN rising UVLO threshold voltage		3.75	3.95	4.15	V
	Hysteresis			100		mV
SUPPLY CURRENT						
lin	IN supply current			160	280	μA
BC 1.2 DCP MODE	(SHORT)					
RDPM_SHORT	DP / DM shorting resistance			125	200	Ω
RDCHG_SHORT	Resistors connected DP /DM to GND after hand-shaking			200	400	kΩ
VDPL_TH_DETACH	DP low threshold while detaching BC1.2 devices		310	330	350	mV
VDPL_TH_DETACH_HYS	hysteresis			50		mV
IPAD MODE 2.1A M	ode (SEL=1 or Floating)					
V _{DP_IPAD}	DP output voltage		2.5	2.7	2.9	V
V _{DM_IPAD}	DM output voltage		1.85	2.0	2.15	V
RDP_IPAD	DP output impedance	I _{DP} = -5uA	20	30	40	kΩ
R _{DM_IPAD}	DM output impedance	I _{DM} = -5uA	20	30	40	kΩ
IPAD MODE 2.4A M	ode (SEL=0)					
V _{DP_IPAD}	DP output voltage		2.5	2.7	2.9	V
V _{DM_IPAD}	DM output voltage		2.5	2.7	2.9	V
R _{DP_IPAD}	DP output impedance	I _{DP} = -5uA	20	30	40	kΩ
R _{DM_IPAD}	DM output impedance	I _{DM} = -5uA	20	30	40	kΩ
Galaxy Tab MODE						
V _{DP_GAL}	DP output voltage		1.1	1.2	1.3	V
V _{DM_GAL}	DM output voltage		1.1	1.2	1.3]
RDP_GAL	DP output impedance	I _{DP} = -5uA	70	105	140	1,0
Rdm_gal	DM output impedance	I _{DM} = -5uA	70	105	140	kΩ

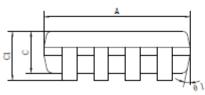


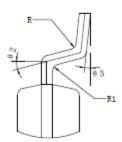
PACKAGE INFORMATION

EMSOP8









标注 尺寸	最小(==)	最大(mm)	标注 尺寸	最小(==)	最大(mm)		
A	2.90	3.10	C3	0.	152		
A1	0.28	0.35	C4	0.15	0.23		
A2	0.6	5TYP	H	0.02	0.15		
A3	0.3	75TYP	θ	12° TYP4			
В	2.90	3.10	0 1	12° TYP4			
B1	4.70	5. 10	θ 2	14	1° TYP		
B2	0.45	0.75	03	0° ~ 6°			
С	0.75	0.95	R	0. 15TYP			
C1	-	1.10	R1	0. 15TYP			
C2	0.3	28TYP					
* 注: EMSO	* 注: EMSOP8产品框架基岛尺寸为1.80X1.80, 散热片尺寸为1.80X1.55 (单位: mm)						